



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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HiPerFRED²

V_{RRM} = 200V
 I_{FAV} = 2x 15A
 t_r = 35ns

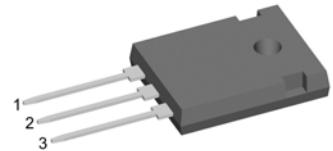
High Performance Fast Recovery Diode

Low Loss and Soft Recovery

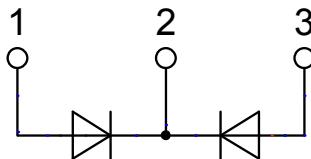
Common Cathode

Part number

DPG30C200HB



Backside: cathode



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low I_{rm} -values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low I_{rm} reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: TO-247

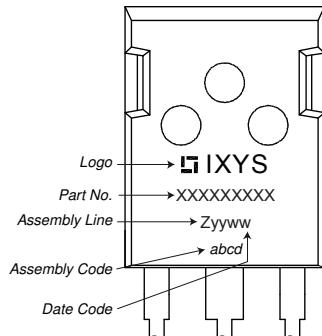
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

Fast Diode

Symbol	Definition	Conditions	Ratings			
			min.	typ.	max.	
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^\circ C$			200	V
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^\circ C$			200	V
I_R	reverse current, drain current	$V_R = 200 V$ $V_R = 200 V$	$T_{VJ} = 25^\circ C$ $T_{VJ} = 150^\circ C$		1 0.08	μA mA
V_F	forward voltage drop	$I_F = 15 A$ $I_F = 30 A$ $I_F = 15 A$ $I_F = 30 A$	$T_{VJ} = 25^\circ C$ $T_{VJ} = 150^\circ C$		1.25 1.50 1.00 1.27	V V V V
I_{FAV}	average forward current	$T_C = 145^\circ C$ rectangular	$T_{VJ} = 175^\circ C$		15	A
I_F	threshold voltage slope resistance	$\left. \right\} \text{for power loss calculation only}$		$T_{VJ} = 175^\circ C$	0.69 17.3	V $m\Omega$
R_{thJC}	thermal resistance junction to case				1.7	K/W
R_{thCH}	thermal resistance case to heatsink			0.25		K/W
P_{tot}	total power dissipation		$T_C = 25^\circ C$		90	W
I_{FSM}	max. forward surge current	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}; V_R = 0 V$	$T_{VJ} = 45^\circ C$		240	A
C_J	junction capacitance	$V_R = 150 V$ $f = 1 \text{ MHz}$	$T_{VJ} = 25^\circ C$	20		pF
I_{RM}	max. reverse recovery current		$T_{VJ} = 25^\circ C$ $T_{VJ} = 125^\circ C$	3 6.5		A A
t_{rr}	reverse recovery time	$I_F = 15 A; V_R = 130 V$ $-di_F/dt = 200 A/\mu s$	$T_{VJ} = 25^\circ C$ $T_{VJ} = 125^\circ C$	35 55		ns ns

Package TO-247			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal ¹⁾			50	A
T_{VJ}	virtual junction temperature		-55		175	°C
T_{op}	operation temperature		-55		150	°C
T_{stg}	storage temperature		-55		150	°C
Weight				6		g
M_D	mounting torque		0.8		1.2	Nm
F_c	mounting force with clip		20		120	N

Product Marking



Part number

D = Diode
 P = HiPerFRED
 G = extreme fast
 30 = Current Rating [A]
 C = Common Cathode
 200 = Reverse Voltage [V]
 HB = TO-247AD (3)

Ordering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DPG30C200HB	DPG30C200HB	Tube	30	505797

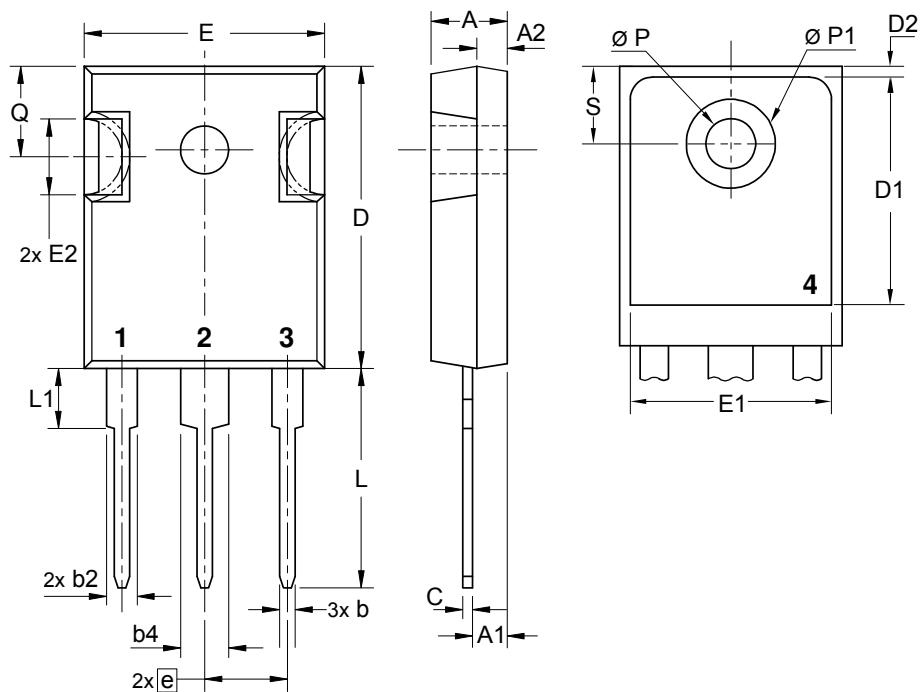
Similar Part	Package	Voltage class
DPG30C200PB	TO-220AB (3)	200
DPG30C200PC	TO-263AB (D2Pak) (2)	200

Equivalent Circuits for Simulation

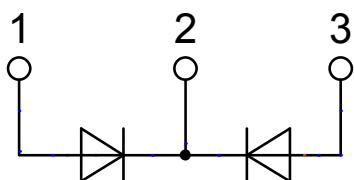
^{*} on die level $T_{VJ} = 175 \text{ }^{\circ}\text{C}$

	Fast Diode	
$V_{0\max}$	threshold voltage	0.69
$R_{0\max}$	slope resistance *	14.7

Outlines TO-247



Sym.	Inches min. max.	Millimeter min. max.
A	0.185 0.209	4.70 5.30
A1	0.087 0.102	2.21 2.59
A2	0.059 0.098	1.50 2.49
D	0.819 0.845	20.79 21.45
E	0.610 0.640	15.48 16.24
E2	0.170 0.216	4.31 5.48
e	0.215 BSC	5.46 BSC
L	0.780 0.800	19.80 20.30
L1	- 0.177	- 4.49
Ø P	0.140 0.144	3.55 3.65
Q	0.212 0.244	5.38 6.19
S	0.242 BSC	6.14 BSC
b	0.039 0.055	0.99 1.40
b2	0.065 0.094	1.65 2.39
b4	0.102 0.135	2.59 3.43
c	0.015 0.035	0.38 0.89
D1	0.515 -	13.07 -
D2	0.020 0.053	0.51 1.35
E1	0.530 -	13.45 -
Ø P1	- 0.29	- 7.39



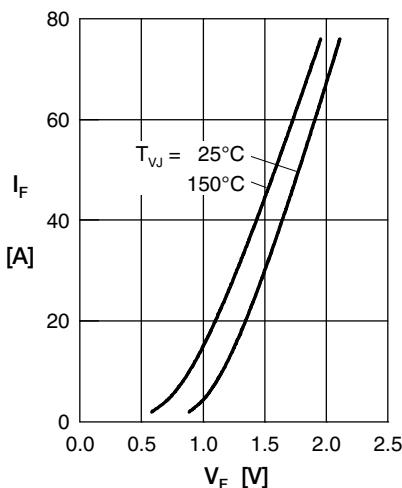
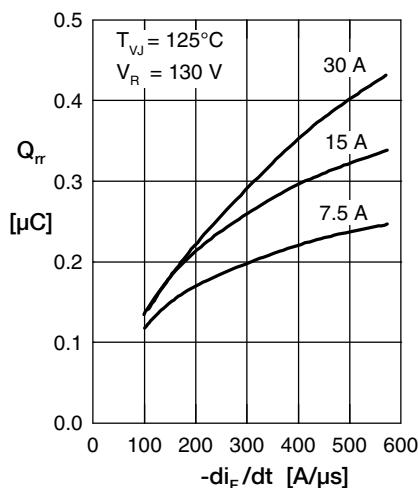
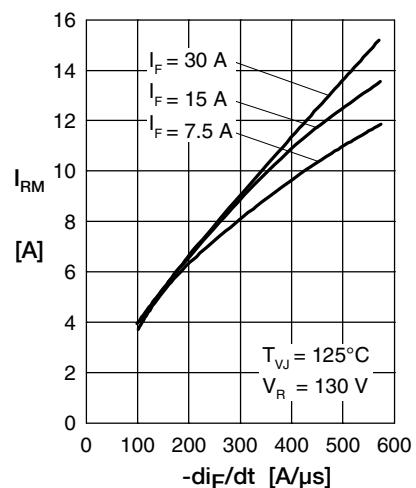
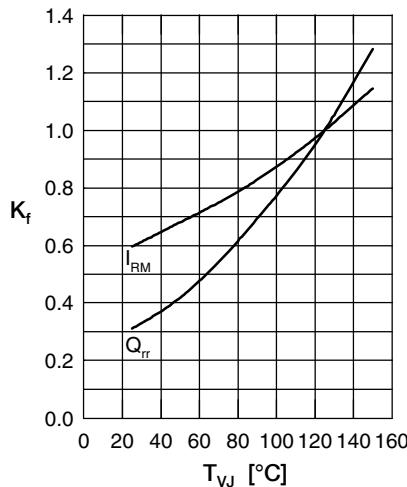
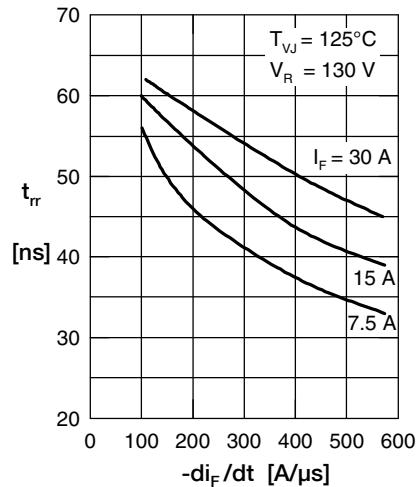
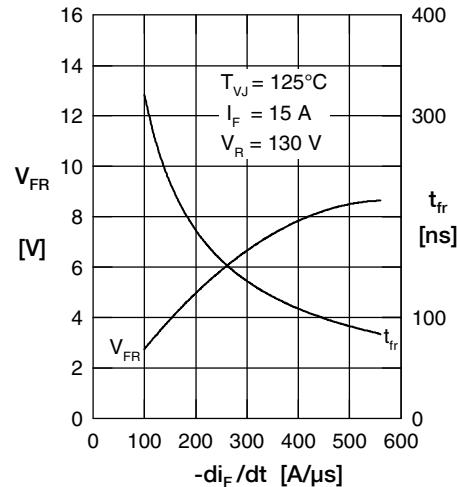
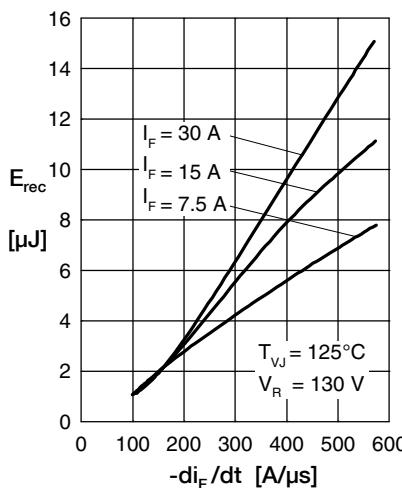
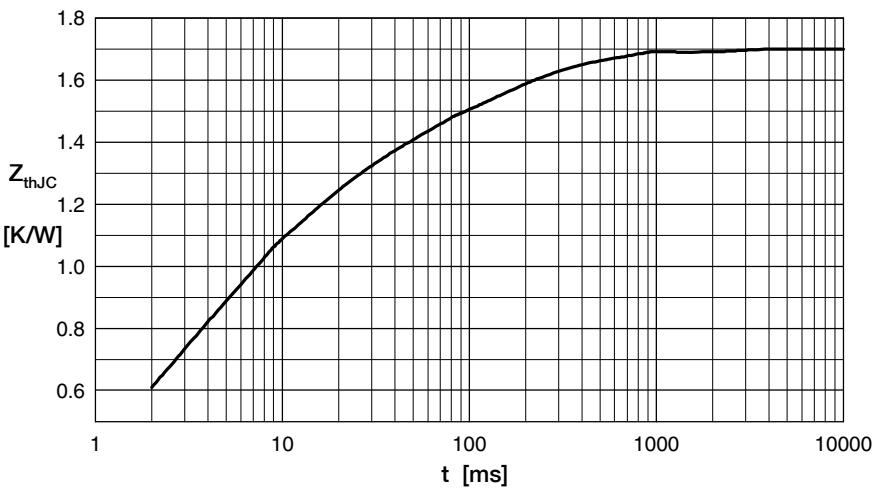
Fast DiodeFig. 1 Forward current I_F versus V_F Fig. 2 Typ. reverse recov. charge Q_{rr} versus $-di_F/dt$ Fig. 3 Typ. peak reverse current I_{RM} versus $-di_F/dt$ Fig. 4 Typ. dynamic parameters Q_{rr} , I_{RM} versus T_{VJ} Fig. 5 Typ. recovery time t_{rr} versus $-di_F/dt$ Fig. 6 Typ. peak forward voltage V_{FR} and t_{fr} versus di_F/dt Fig. 7 Typ. recovery energy E_{rec} versus $-di_F/dt$ 

Fig. 8 Transient thermal resistance junction to case